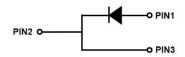




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F(135°C)}	3.4A
Qc	10.2nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25 °C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112002DYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _c =25°C		А	7
Continuous forward current @ T _c =135°C	I _F		3.4
Continuous forward current @ T _C =159°C			2
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	20
Power Dissipation@ T _c =25°C	D	W	42
Power Dissipation@ T _C =110°C	Р _{тот}		18.2
i²t Value@ T _C =25°C ,tp=10ms	∫i²dt	A ² S	2
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =2A, T _j =25°C	1.45	1.60
			I _F =2A, T _j =175°C	2.17	-
Reverse current	I _R	μА	V _R =1200V, T _j =25°C	0.1	20
			V _R =1200V, T _j =175°C	0.5	-
Total capacitive charge	Q _C	nC	$\begin{array}{c} V_R = 800V, \ T_j = 25^{\circ}C \ , \\ Q_C = \int_0^{VR} C(V) dV \end{array}$	10.2	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	127	-
			V _R =400V, f=1MHZ	9.8	-
			V _R =800V, f=1MHZ	7.5	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	2.6	-

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{ heta J-C}$	°C W	3.57

■Typical Characteristics

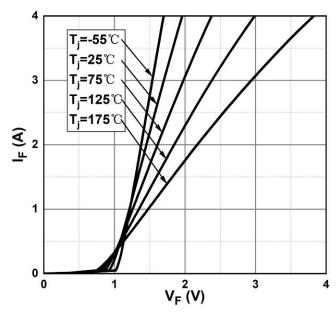


Figure 1. Forward Characteristics

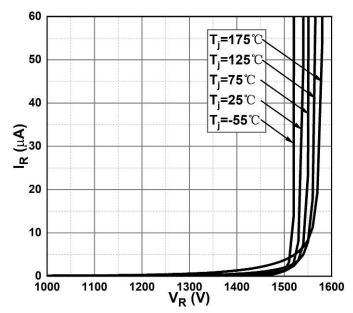
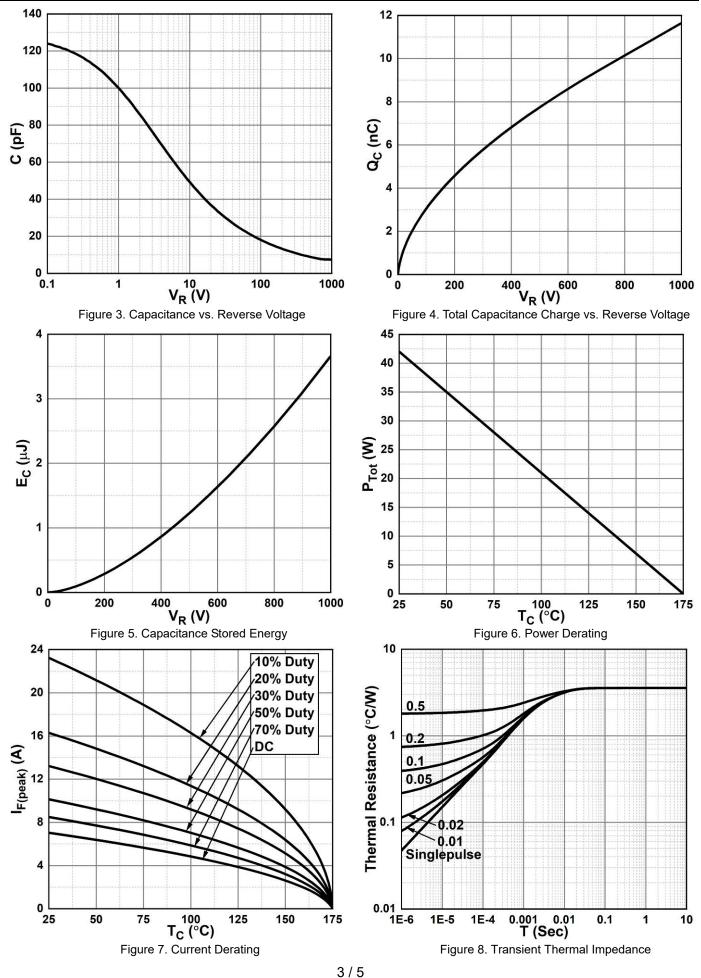


Figure 2. Reverse Characteristics

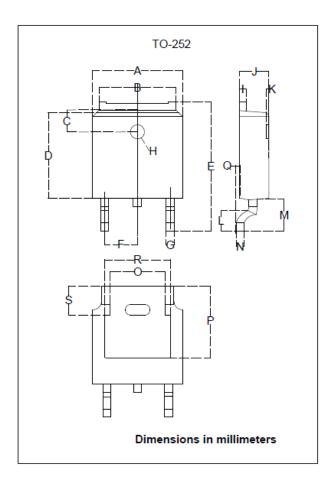








■Outline Dimensions



TO-252			
Dim	Min	Max	
Α	6.500	6.700	
В	5.100	5.460	
С	1.400	1.800	
D	6.000	6.200	
E	10.000	10.400	
F	2.166	2.366	
G	0.660	0.860	
Н	Ф1.050	Ф1.350	
I	0.460	0.580	
J	2.200	2.400	
K	0	0.300	
L	0.890	2.290	
М	2.730	3.080	
N	0.430	0.580	
0	4.20	4.95	
Р	5.15	5.45	
Q	0	0.2	
R	4.50	5.10	
S	1.60	2.40	



YJD112002DYG4

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